



60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

4 A

Features

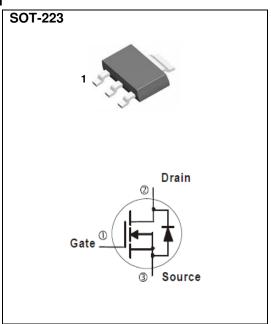
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@3A<100m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@2A<110m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: SOT-223 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.043 ounces, 0.123grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	60	- v	
Gate-Source Voltage		V_{GS}	<u>+</u> 20		
Continuous Drain Current (Note 4)	T _A =25°C	- I _D	4		
	T _A =70°C		3.2	Α	
Pulsed Drain Current (Note 1)		I _{DM}	8		
Power Dissipation	T _A =25°C	P_{D}	3.7	W	
	T _A =70°C		2.6		
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~175	°C	
Typical Thermal Resistance					
- Junction to Ambient (Note 4,5)		$R_{\theta JA}$	40.3	°C/W	

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	$V_{GS} = 0V, I_D = 250uA$		-	-	. v	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1	1.86	2.5	V	
Drain-Source On-State Resistance	R _{DS(on)}	$V_{GS}=10V$, $I_D=3A$	-	85	100		
		V_{GS} =4.5V, I_D =2A	-	95	110	mΩ	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =48V, V_{GS} =0V	-	-	1	uA	
Gate-Source Leakage Current	I _{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	ı	<u>+</u> 100	nA	
Dynamic (Note 6)							
Total Gate Charge	Qg	V _{DS} =48V, I _D =3A, V _{GS} =4.5V (Note 2,3)	-	5.1	-	nC	
Gate-Source Charge	Q_{gs}		-	1.2	-		
Gate-Drain Charge	Q_{gd}		-	1.9	-		
Input Capacitance	Ciss	V _{DS} =15V, V _{GS} =0V,	-	509	-	pF	
Output Capacitance	Coss		-	39	-		
Reverse Transfer Capacitance	Crss	I=IIVIMZ	-	26	-		
Turn-On Delay Time	td _(on)	V_{DD} =30V, I_{D} =3A, V_{GS} =10V, R_{G} =3.3 Ω (Note 2,3)	-	1.6	-	ns	
Turn-On Rise Time	t _r		-	7.3	-		
Turn-Off Delay Time	td _(off)		-	25	-		
Turn-Off Fall Time	t _f	n _G =3.312	-	14	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	,				4	_	
Diode Forward Current	I _S		-	-	4	Α	
Diode Forward Voltage	V_{SD}	I _S =1A, V _{GS} =0V	_	0.8	1.2	V	

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150$ °C. Ratings are based on low frequency and duty cycles to keep initial $T_J=25$ °C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

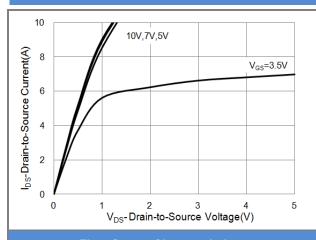
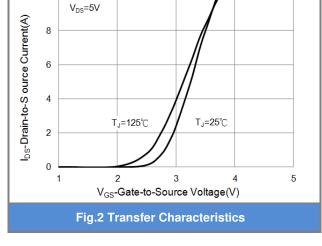


Fig.1 Output Characteristics



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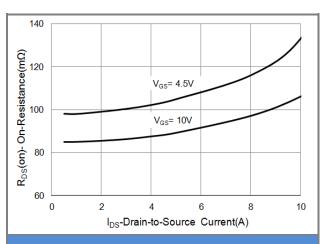


Fig.3 On-Resistance vs. Drain Current

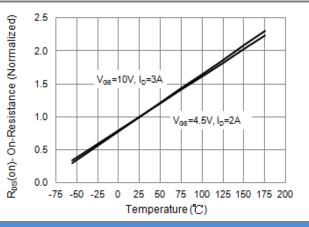
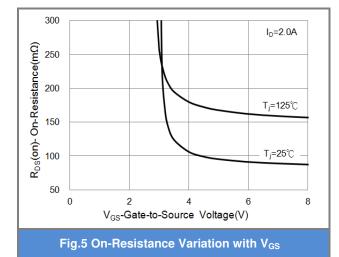


Fig.4 On-Resistance vs. Junction temperature



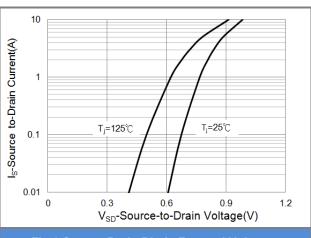


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

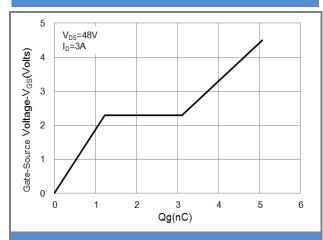


Fig.7 Gate-Charge Characteristics

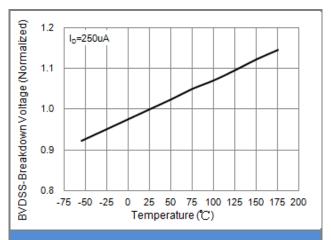


Fig.8 Breakdown Voltage Variation vs. Temperature

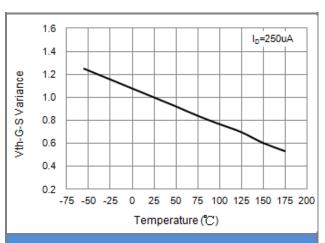


Fig.9 Threshold Voltage Variation with Temperature

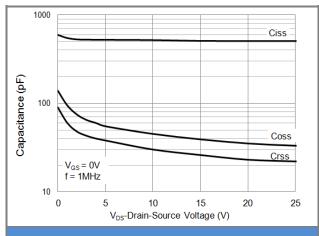


Fig.10 Capacitance vs. Drain-Source Voltage

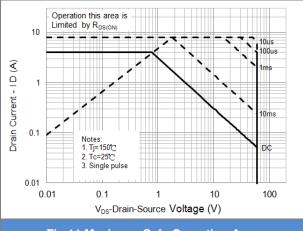


Fig.11 Maximum Safe Operating Area





TYPICAL CHARACTERISTIC CURVES

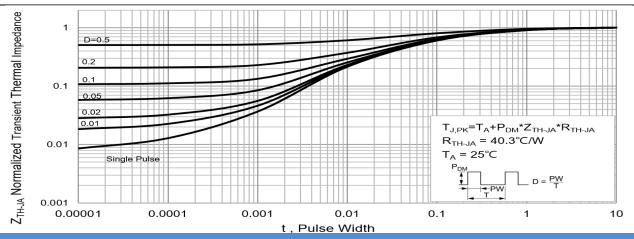


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

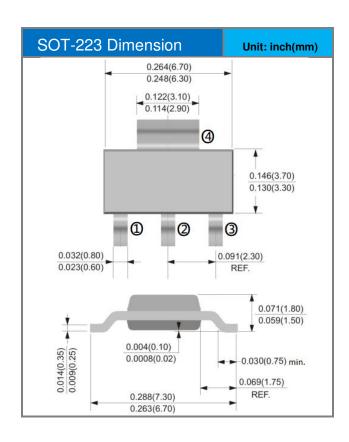


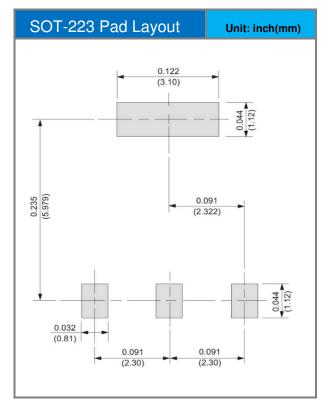


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJW4N06A-AU_R2_000A1	SOT-223	2,500pcs / 13" reel	W4N06A	Halogen free

Packaging Information & Mounting Pad Layout









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